



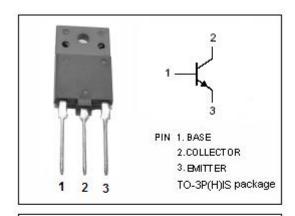
# **isc** Silicon NPN Power Transistor

## **DESCRIPTION**

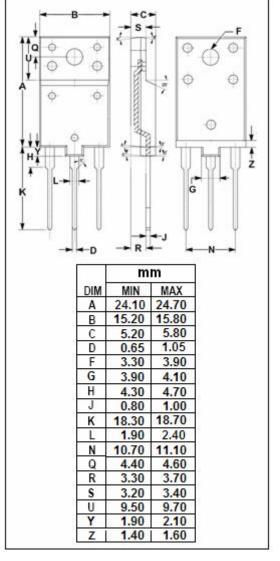
- High Breakdown Voltage
- · High Switching Speed
- Wide Area of Safe Operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

• Designed for horizontal deflection output applications.



| ABSOLUTE MAXIMUM RATINGS(Ta=25℃) |   |         |              |  |  |  |  |
|----------------------------------|---|---------|--------------|--|--|--|--|
| SYMBOL                           | PARAMETER   | VALUE   | UNIT         |  |  |  |  |
| Vсво                             | Collector-Base Voltage                            | 1700    | V            |  |  |  |  |
| V <sub>CES</sub>                 | Collector-Emitter Voltage                         | 1700    | ٧            |  |  |  |  |
| V <sub>CEO</sub>                 | Collector-Emitter Voltage                         | 600     | V            |  |  |  |  |
| V <sub>EBO</sub>                 | Emitter-Base Voltage                              | 5       | V            |  |  |  |  |
| Ic                               | Collector Current- Continuous                     | 15      | А            |  |  |  |  |
| Ісм                              | Collector Current- Peak                           | 20      | А            |  |  |  |  |
| lв                               | Base Current- Continuous                          | 8       | А            |  |  |  |  |
| P <sub>C</sub>                   | Collector Power Dissipation @ T <sub>c</sub> =25℃ | 100     | 10/          |  |  |  |  |
|                                  | Collector Power Dissipation @ T <sub>a</sub> =25℃ | 3       | W            |  |  |  |  |
| TJ                               | Junction Temperature 1                            |         | $^{\circ}$ C |  |  |  |  |
| T <sub>stg</sub>                 | Storage Temperature Range                         | -55~150 | $^{\circ}$ C |  |  |  |  |
|                                  |   |         |              |  |  |  |  |





## **ISC Silicon NPN Power Transistor**

2SC5407

#### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

| SYMBOL                | PARAMETER                            | CONDITIONS   | MIN | TYP. | MAX       | UNIT       |  |  |  |
|-----------------------|--------------------------------------|--|-----|------|-----------|------------|--|--|--|
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 7.5A; I <sub>B</sub> = 1.88A  |     |      | 3.0       | V          |  |  |  |
| V <sub>BE</sub> (sat) | Base-Emitter Saturation Voltage      | I <sub>C</sub> = 7.5A; I <sub>B</sub> = 1.88A  |     |      | 1.5       | V          |  |  |  |
| Ісво                  | Collector Cutoff Current             | V <sub>CB</sub> = 1000V; I <sub>E</sub> = 0<br>V <sub>CB</sub> = 1700V; I <sub>E</sub> = 0 |     |      | 50<br>1.0 | μ A<br>mA  |  |  |  |
| I <sub>EBO</sub>      | Emitter Cutoff Current               | V <sub>EB</sub> = 5V; I <sub>C</sub> = 0   |     |      | 50        | μА         |  |  |  |
| h <sub>FE</sub>       | DC Current Gain                      | I <sub>C</sub> = 7.5A; V <sub>CE</sub> = 5V  | 6   |      | 14        |            |  |  |  |
| f⊤                    | Current-Gain—Bandwidth Product       | Ic= 0.5A; V <sub>CE</sub> = 10V  |     | 3    |           | MHz        |  |  |  |
| Switching Times       |                                      |  |     |      |           |            |  |  |  |
| t <sub>stg</sub>      | Storage Time                         |  |     |      | 4.0       | μ <b>S</b> |  |  |  |
| t <sub>f</sub>        | Fall Time                            | I <sub>C</sub> = 8A, I <sub>B1</sub> = 2A; I <sub>B2</sub> = -4A                           |     |      | 0.3       | μ <b>S</b> |  |  |  |

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